



Silicon PNP Alloy Junction Transistors

DESCRIPTION:

These Hughes® silicon alloy-junction transistors are PNP types intended primarily for switching and amplifying at low and medium current levels at moderate speeds.

These units are characterized by low saturation resistance, medium current handling capabilities, low collector-to-emitter cutoff currents and high collector-to-emitter operating voltages.

Transistors in this series are available in two package styles thus allowing freedom in circuit design based on your individual needs. Types 2N1228 through 2N1234 are assembled into the TO-5 package; 2N1238 through 2N1244 are in the Hughes coaxial package. The sturdy structure of each case style enables them to pass easily the stringent requirements outlined in MIL-S-19500B.



TO-5 Package

Coaxial Package

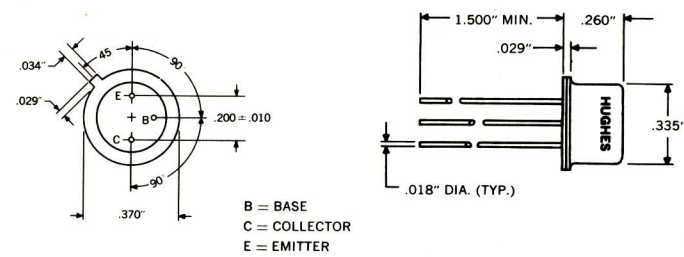
ABSOLUTE MAXIMUM RATINGS @ 25° C.

		2N1228	2N1229	2N1230	2N1231	2N1232	2N1233	2N1234	TO-5 Package
Unit		2N1238	2N1239	2N1240	2N1241	2N1242	2N1243	2N1244	Coaxial Package
Collector to Base Voltage (BV_{CBO})	V	15	15	35	35	60	60	110	
Emitter to Base Voltage (BV_{EBO})	V	15	15	35	35	60	60	110	
Collector to Emitter Voltage (BV_{CEO})	V	15	15	35	35	60	60	110	

Power Dissipation: Coaxial Package—1 watt (free air), derate 7.4 mw/°C; 5 watts (heat sink), derate 37 mw/°C
TO-5 Package—400 mw (free air), derate 3.0 mw/°C

SPECIFICATIONS

DIMENSIONS *maximum unless otherwise stated*

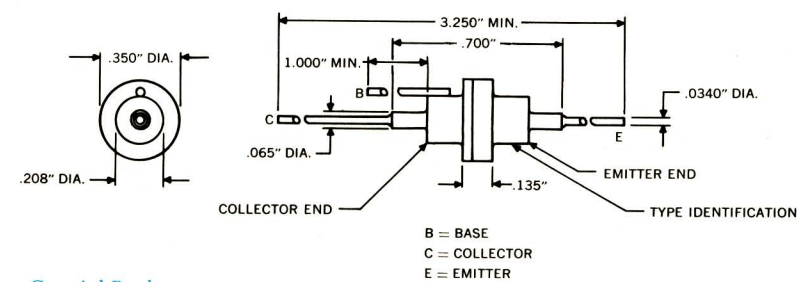


TO-5 Package

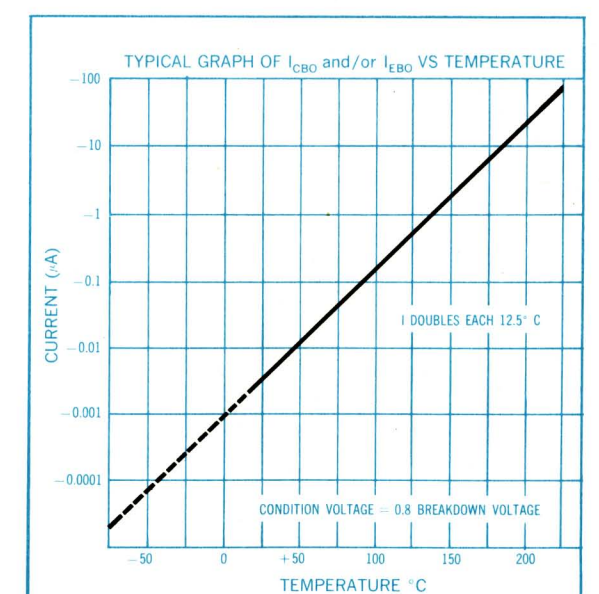
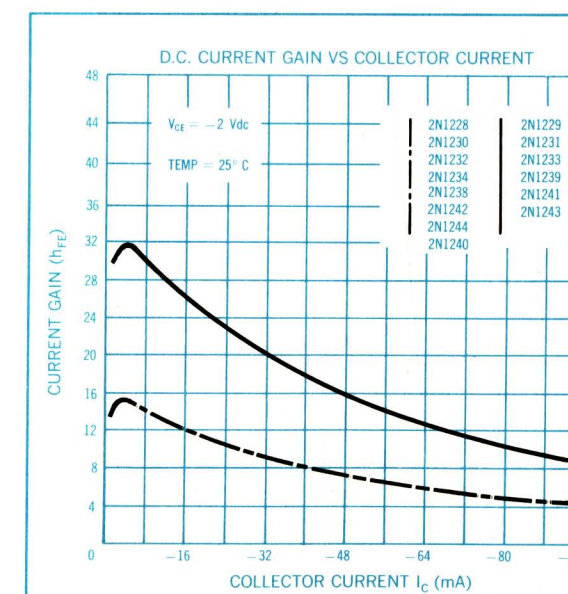
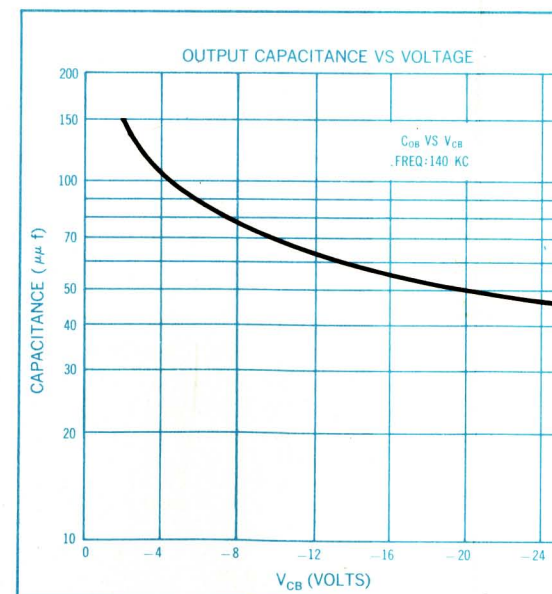
D.C. CHARACTERISTICS	Conditions	Symbol	Unit	2N1228 2N1238	2N1229 2N1239	2N1230 2N1240	2N1231 2N1241	2N1232 2N1242	2N1233 2N1243	2N1234 2N1244
				min typ max	min typ max	min typ max	min typ max	min typ max	min typ max	min typ max
D.C. Current Gain	$V_{CE} = -2V$ $I_C = -10mA$	h_{FE}		14	30	14	30	14	30	14
Collector & Emitter Cutoff Current	$V_{CB} = -12V, 30V$ 50V, 90V	$I_{CBO}; I_{EBO}$	μA_{dc}	-0.01 -0.1 (@-12Vdc)	-0.01 -0.1 (@-12Vdc)	-0.01 -0.1 (@-30Vdc)	-0.01 -0.1 (@-30Vdc)	-0.01 -0.1 (@-50Vdc)	-0.01 -0.1 (@-50Vdc)	-0.01 -0.1 (@-90Vdc)
Collector to Emitter Saturation Voltage	$I_C = -10mA$ $I_B = -2mA$	V_{CE}	Vdc	-0.1 -0.2	-0.1 -0.2	-0.1 -0.2	-0.1 -0.2	-0.1 -0.2	-0.1 -0.2	-0.1 -0.2
Base to Emitter Saturation Voltage	$I_C = -10mA$ $I_B = -2mA$	V_{BE}	Vdc	-0.7 -1.3	-0.7 -1.3	-0.7 -1.3	-0.7 -1.3	-0.7 -1.3	-0.7 -1.3	-0.7 -1.3
SMALL SIGNAL CHARACTERISTICS Frequency Cutoff	$V_{CB} = -5V$ $I_E = 1mA$		Mc	1.2	1.2	1.2	1.2	1.0	1.0	0.8
A.C. Current Gain, Maximum	See Note 1	h_{fe}		14 32	28 65	14 32	28 65	14 32	28 65	14 32
Input Impedance	See Note 1	h_{ib}	ohms	30	30	30	30	30	30	30
Output Admittance	See Note 1	h_{ob}	$\mu mhos$	1.2	1.2	1.2	1.2	1.2	1.2	1.2
Reverse Transfer Voltage Ratio	See Note 1	h_{rb}		15×10^{-4}	15×10^{-4}	8×10^{-4}	8×10^{-4}	4×10^{-4}	4×10^{-4}	4×10^{-4}
Collector Output Capacity	See Note 1	C_{ob}	$\mu \mu f$	95	95	95	95	95	95	95
Noise Figure	See Note 1	NF	db	10	10	10	10	10	10	10

Note: 1. $V_{CB} = -5V$; $I_E = 1mA_{dc}$; $F = 1Kc$

TYPICAL CHARACTERISTICS



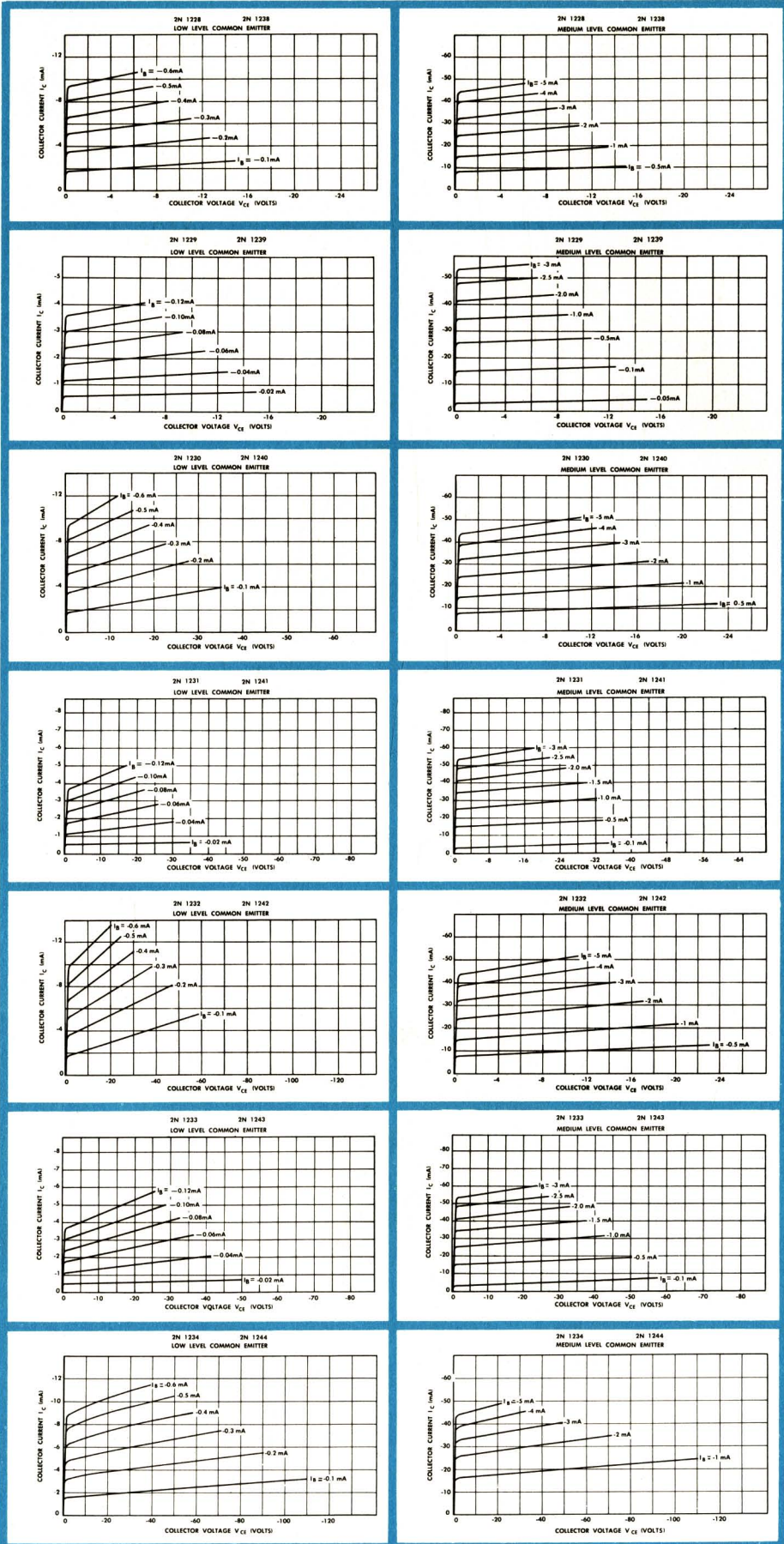
Coaxial Package



COLLECTOR CHARACTERISTICS @25°C.

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HUGHES
Semiconductor Division
HUGHES AIRCRAFT COMPANY
Newport Beach, California



Collector current limited by power dissipation

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